

REMARKS**1. Allowable subject matter:**

5 *Claim 5, 12 objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.*

10 The Applicants note the Examiner's comments remarks regarding allowable subject matter upon first consideration of the instant application.

2. Claim rejections – 35 USC § 102:

15 *Claims 1-4 and 6-11 are rejected under 35 USC 102 (b) as being anticipated by Goo (U.S. Patent 5,677,215).*

Response:

20 Regarding claims 1-4, during the following discussion, the Applicants will endeavor to clearly state the salient differences between the cited prior art, Goo (U.S. Patent 5,677,215) – herein after referred to as Goo, and the claimed invention embodiment recited by claims 1-4.

25 The Applicants point out that while Goo is primarily directed at a more efficient manufacturing method for a semiconductor memory device, the present invention is directed at increasing the density of such memory devices by providing a single instance of a ROM cell disposed on a semiconductor substrate with multiple drain signals, instead of the single drain signal of the prior art, thereby enabling the ROM cell of the present invention to store more than one data bit.

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 Claim 1 of the instant invention can be understood from Fig.2 and Fig.3 although claim 1 is not limited to the embodiment in these figures. Figs.2 and 3 clearly show a

drain doped region (210), this recited as "a first doped region being of a second
conductive type installed on the silicon substrate", and further heavily doped regions
(212a & 212b) of a different conductive type formed in the drain doped region (210),
these being recited as "a plurality of first heavily doped regions being of a first
5 conductive type installed in the first doped region". Whereas, Goo teaches only a
single heavily doped area actually within the first doped region, as is required to
create a prior art semiconductor memory, the second heavily doped area (as can be
seen from Fig.4 of the cited art) being elsewhere on the substrate. The arrangement
taught by Goo and consequently a device formed according to Goo's teachings may
10 only provide a single drain signal and therefore can only store a single data bit. The
teachings of Goo cannot realize the present invention capability of storing multiple
data bits.

The Applicant therefore asserts that claim 1 of the present invention is not
15 anticipated by Goo, reconsideration of claim 1 is politely requested in light of the
above discussion.

Claims 2-5, being dependent upon claim 1, should be allowed if claim 1 is found
to be allowable.

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Regarding claims 6-11, all limitations of claim 12 are hereby included in the base
claim, claim 6, as suggested and claim 12 is hereby cancelled. Since claim 12 is
objected to as being dependent upon a rejected base claim, but would be allowable if
rewritten in independent form including all of the limitations of the base claim and
25 any intervening claims, allowance of the amended claim 6 is hereby requested. The
amended claim 7 and claims 8-11, being dependent upon the amended claim 6 and
should be allowable if the amended claim 6 is allowed. Allowance of the amended
claim 7 and claims 8-11 is politely requested.

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Sincerely,

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